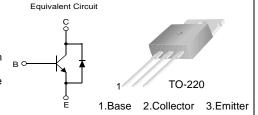
Rev. A1, June 2001



KSC5302D

High Voltage High Speed Power Switch Application

- High Breakdown Voltage: BV_{CBO}=800V
 Built-in Free-wheeling Diode makes efficient anti saturation operation
 Suitable for half bridge light ballast Applications
- No need to interest an hFE value because of low variable storage-time spread
- Even though corner spirit product
- Low base drive requirement



NPN Silicon Transistor

Absolute Maximum Ratings T_C=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	800	V
V _{CEO}	Collector-Emitter Voltage	400	V
V _{EBO}	Emitter-Base Voltage	12	V
I _C	Collector Current (DC)	2	Α
I _{CP}	*Collector Current (Pulse)	5	Α
I _B	Base Current (DC)	1	Α
I _{BP}	*Base Current (Pulse)	2	Α
P _C	Power Dissipation(T _C =25°C)	50	W
TJ	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 55 ~ 150	°C

Thermal Characteristics $T_C=25$ °C unless otherwise noted

Symbol	Characteristics		Rating	Unit
$R_{\theta jc}$	Thermal Resistance	Junction to Case	2.5	°C/W
$R_{\theta ja}$		Junction to Ambient	62.5]

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Electrical Characteristics $\rm T_{C}{=}25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	I _C =1mA, I _E =0	800	-	-	V
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C =5mA, I _B =0	400	-	-	V
BV _{EBO}	Emitter Cut-off Current	I _E =1mA, I _C =0	12	-	-	V
I _{CBO}	Collector Cut-off Current	V _{CB} =500V, I _E =0	-	-	10	μА
I _{EBO}	Emitter Cut-off Current	$V_{EB} = 9V, I_{C} = 0$	-	-	10	μΑ
h _{FE1}	DC Current Gain	V _{CE} =1V, I _C =0.4A	20	-	-	
h _{FE2}		V _{CE} =1V, I _C =1A	10	-	-	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C =0.4A, I _B =0.04A	-	-	0.4	V
		I _C =1A, I _B =0.2A	-	-	0.5	V
V _{BE} (sat)	Base-Emitter Saturation Voltage	I _C =0.4A, I _B =0.04A	-	-	0.9	V
		I _C =1A, I _B =0.2A	-	-	1.0	V
C _{ob}	Output Capacitance	V _{CB} = 10V, f=1MHz	-	-	75	pF
t _{ON}	Turn ON time	$V_{CC} = 300V, I_{C} = 1A$	-	-	150	ns
t _{STG}	Storage Time	$I_{B1} = 0.2A, I_{B2} = -0.5A,$	-	-	2	μs
t _F	Fall Time	$R_L = 300\Omega$	-	-	0.2	μs
t _{STG}	Storage Time	V _{CC} =15V, V _Z =300V	-	-	2.35	μs
t _F	Fall Time	$I_C = 0.8A, I_{B1} = 0.16A$ $I_{B2} = -0.16A, L = 200\mu H$	-	-	150	ns
V _F	Diode Forward Voltage	I _F = 0.4A	-	-	1.2	V
•		I _F = 1A	-	-	1.5	V
t _{rr}	*Reverse Recovery Time	I _F = 0.2A	-	800	-	ns
	$(di/dt = 10A/\mu s)$	I _F = 0.4A	-	1	-	μs
		I _F = 1A	-	1.4	-	μs

*Pulse Test : Pulse Width=5mS, Duty cycles ≤ 10%

Typcial Characteristics

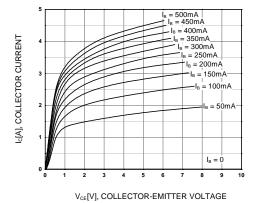


Figure 1. Static Characteristic

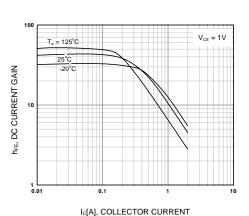


Figure 3. DC current Gain

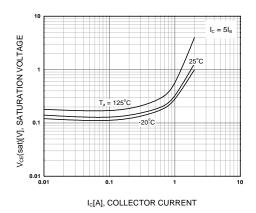


Figure 5. Collector-Base Saturation Voltage

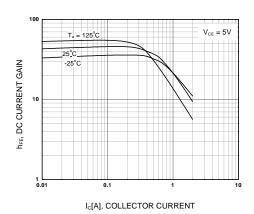


Figure 2. DC current Gain

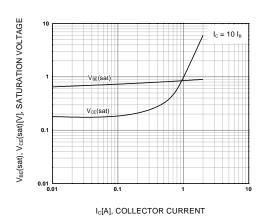


Figure 4. Collector-Emitter Saturation Voltage Base-Emitter Saturation Voltage

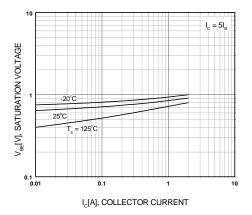


Figure 6. Base-Emitter Saturation Voltage

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Typical Characteristics (Continued)

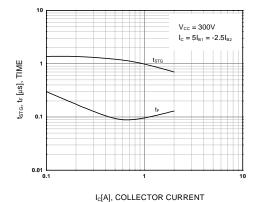


Figure 7. Switching Time

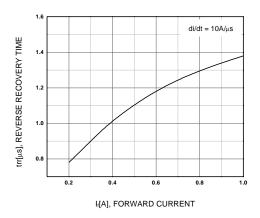


Figure 9. Reverse Recovery Time

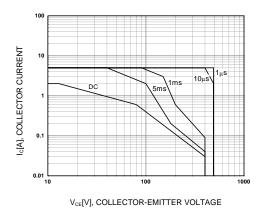


Figure 11. Safe Operating Area

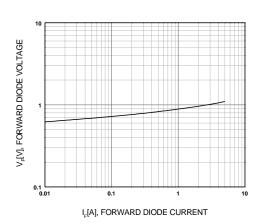


Figure 8. Forwrd Diode Voltage

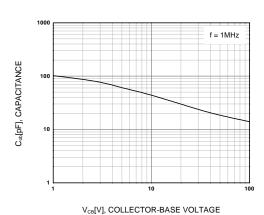


Figure 10. Collector Outpt Capacitance

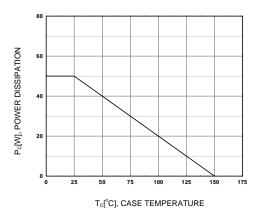
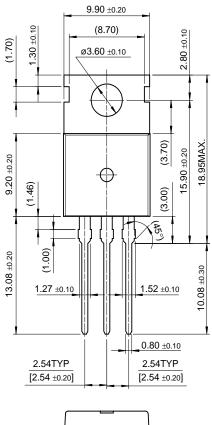
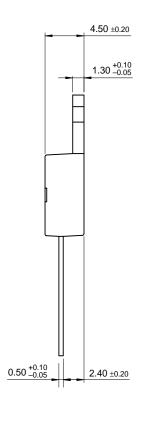


Figure 12. Power Derating

Package Demensions

TO-220





10.00 ±0.20

Dimensions in Millimeters

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